Reply to Final Office Action of November 28, 2008

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently Amended) A silicon based thin film solar cell, wherein a conducted type silicon based low refractive index layer, a silicon based interface layer, and a back electrode are disposed and contact one another in this order on a backside of a photoelectric conversion layer observed from a light incident side.
- 2. (Original) The silicon based thin film solar cell according to Claim 1, wherein the silicon based low refractive index layer has a refractive index not more than 2.5 at a wavelength of 600 nm.
- 3. (Previously Presented) The silicon based thin film solar cell according to Claim 1, wherein a most abundantly existing constituent element, excluding silicon, in the silicon based low refractive index layer is not less than 25 atomic %.
- 4. (Original) The silicon based thin film solar cell according to claim 3, wherein the most abundantly existing constituent element is oxygen.
- 5. (Previously Presented) The silicon based thin film solar cell according to Claim 1, wherein the silicon based low refractive index layer has a thickness of not less than 300 angstroms.
- 6. (Previously Presented) The silicon based thin film solar cell according to Claim 1, wherein the silicon based low refractive index layer comprises a crystalline silicon component in the layer.

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7. (Previously Presented) The silicon based thin film solar cell according to Claim 1, wherein the silicon based interface layer has a thickness not more than 150 angstroms.

- 8. (Original) The silicon based thin film solar cell according to Claim 7, wherein the silicon based interface layer comprises a crystalline silicon component in the layer.
- 9. (New) The silicon based thin film solar cell according to Claim 1, wherein the silicon based low refractive index layer and silicon based interface layer includes the same conductivity type.